

Supporting Information

Conductive Layer Protected and Oxide Catalyst Coated Thin-Film Silicon Solar Cell as Efficient Photoanode

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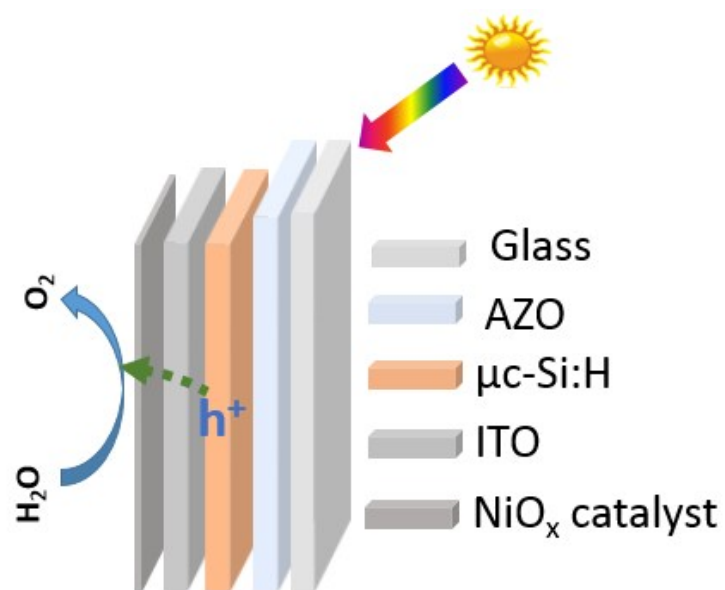


Figure S1. The scheme structure of $\mu\text{c-Si:H}$ solar cell photoanode.

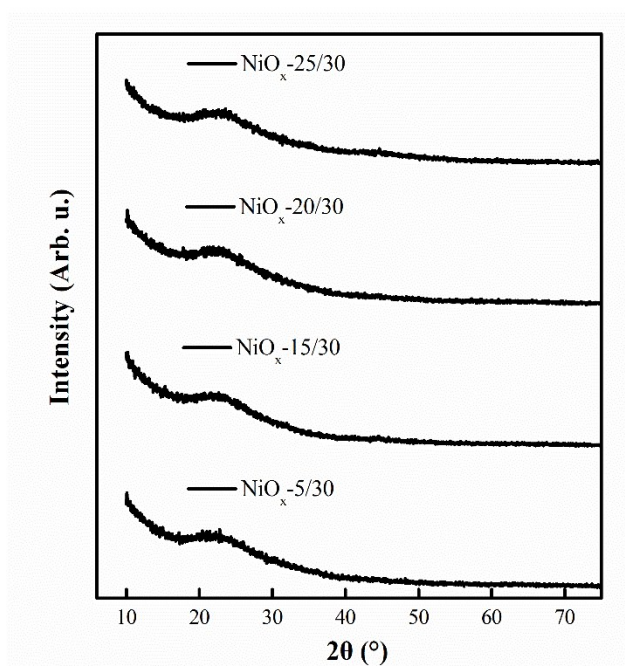


Figure S2. The XRD patterns of NiO_x catalysts with different O_2/Ar .

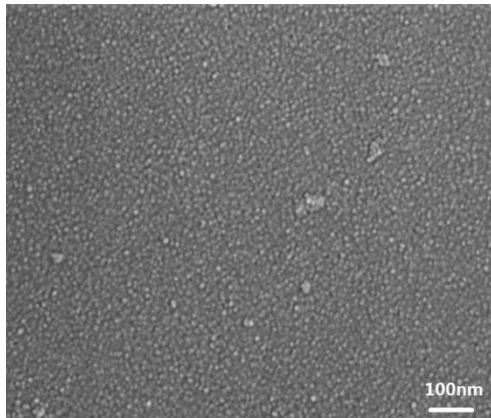


Figure S3. The surface SEM image of NiO_x-20/30.

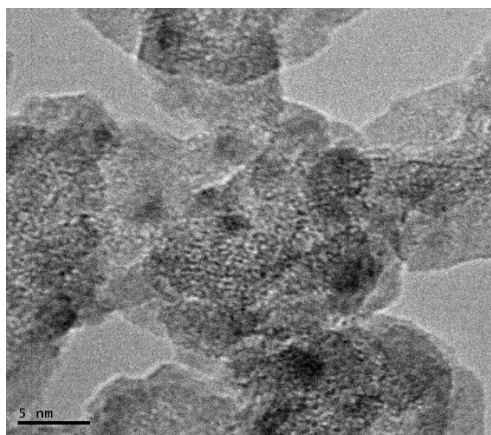


Figure S4. The TEM image of NiO_x-20/30.

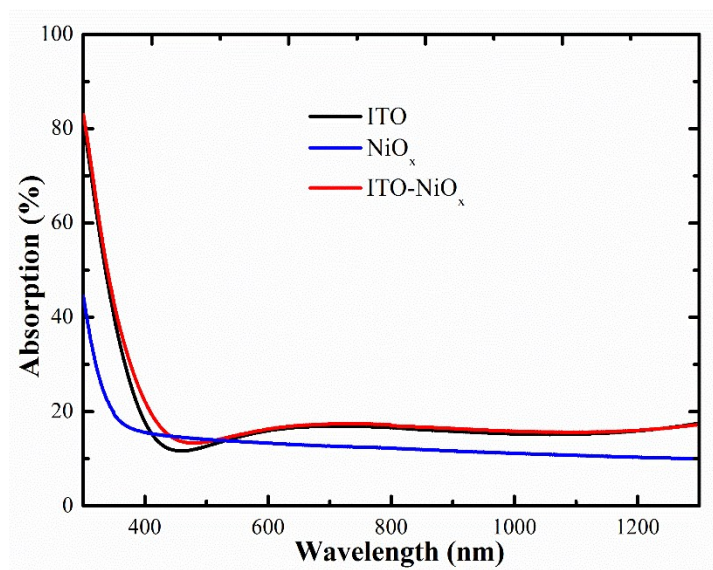


Figure S5. The absorption curves of the ITO layer, NiO_x catalyst and the combination of ITO and NiO_x-20/30 layer.

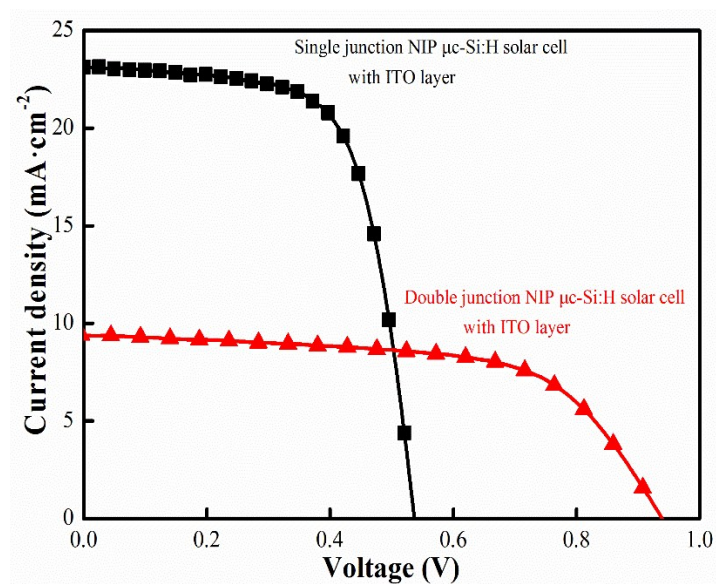


Figure S6. The I-V curves of single junction NIP and double junction NIP $\mu\text{-Si:H}$ solar cells with ITO layer.